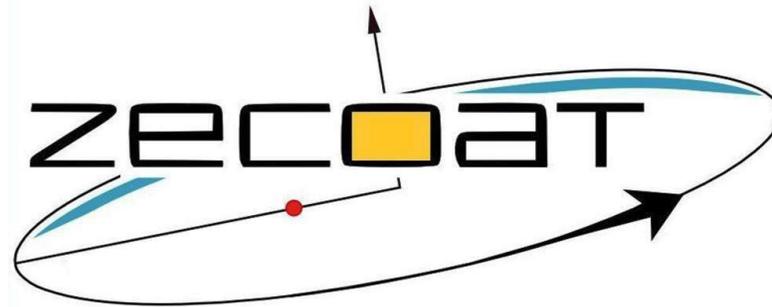


Low-Stress Silicon Cladding for Surface Finishing Large UVOIR Mirrors NASA

SBIR Phase II contract No. NNX14CP14
Technical Monitor: Dr. David Redding (JPL)



PI: David A. Sheikh

ZeCoat Corporation

11/20/2014

Introduction

- In this presentation, I will discuss the status of our Phase II silicon cladding development effort, which is based on ion-assisted, physical evaporation (PV)
- The coating area is currently 1.2-meter in diameter and we are considering options for demonstrating coating a larger area (2-meter +)
- Future large telescopes may be monolithic (4-meters or larger), or comprised of many smaller segments (~1.5-m).

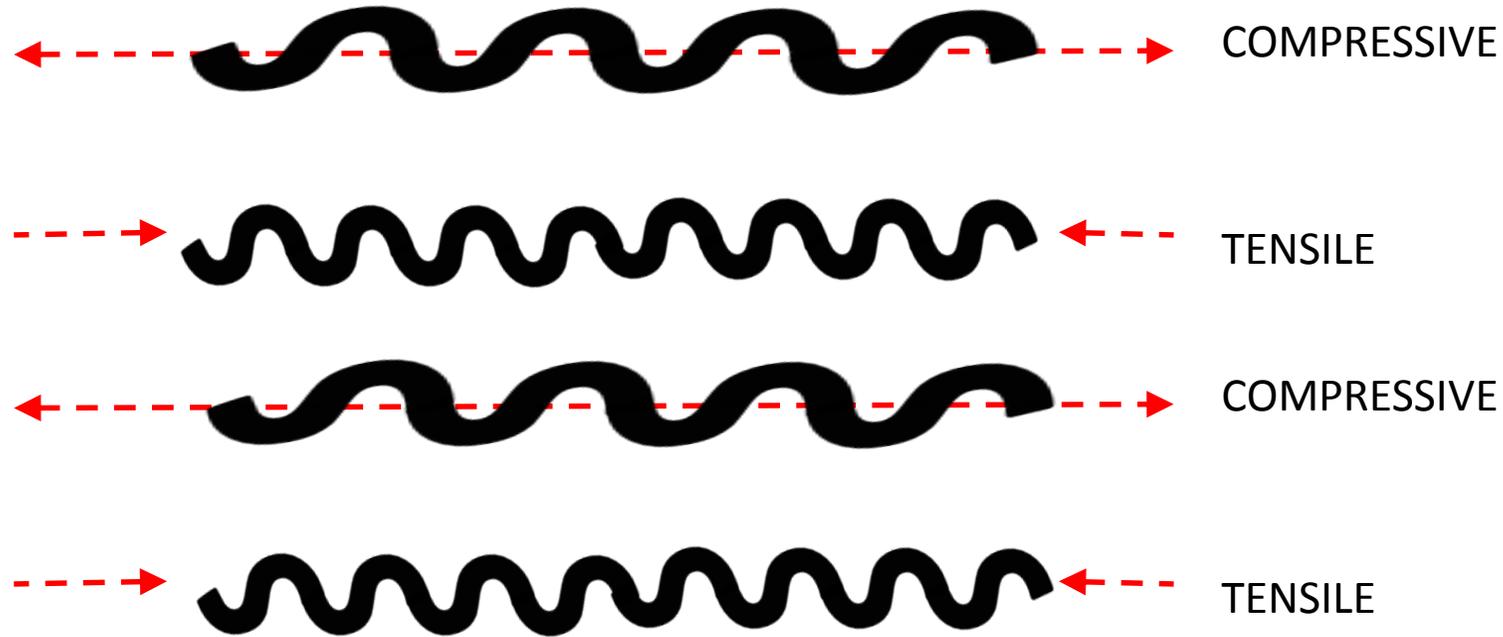
What is Silicon Cladding?

- Silicon cladding is a material applied on the surface of a SiC mirror substrate, to provide a better surface to polish and to reduce figuring time
- A 10 to 100-micron silicon layer is typically applied on top of the SiC
- Why Silicon? Good material to diamond turn or polish, and the CTE is very close to SiC

Research Goals

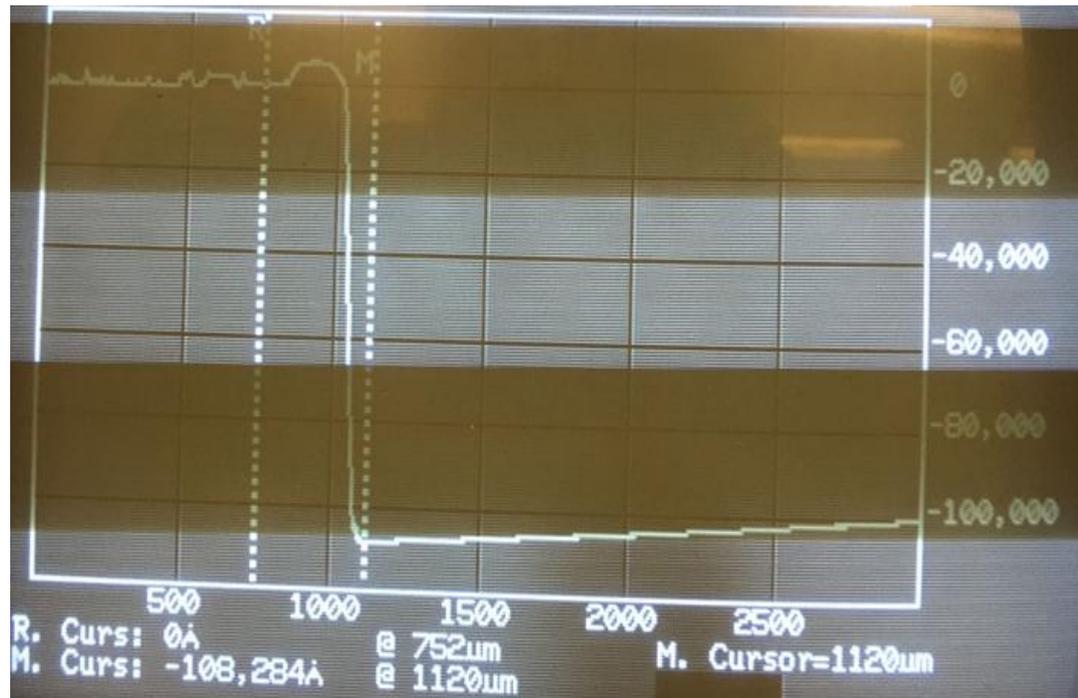
- Create a viable cladding production process for large mirrors
- Create a process that is scalable to ANY size vacuum chamber
- Create a “turn-key” technology suitable for licensing to silicon carbide mirror manufacturers
 - ZeCoat 2nd source supplier
 - ZeCoat R&D

ZeCoat's Si cladding process is based on periodically alternating the sign of the coating stress to yield a near-zero net coating stress. IAD silicon has compressive stress and non-IAD silicon has natural tensile stress

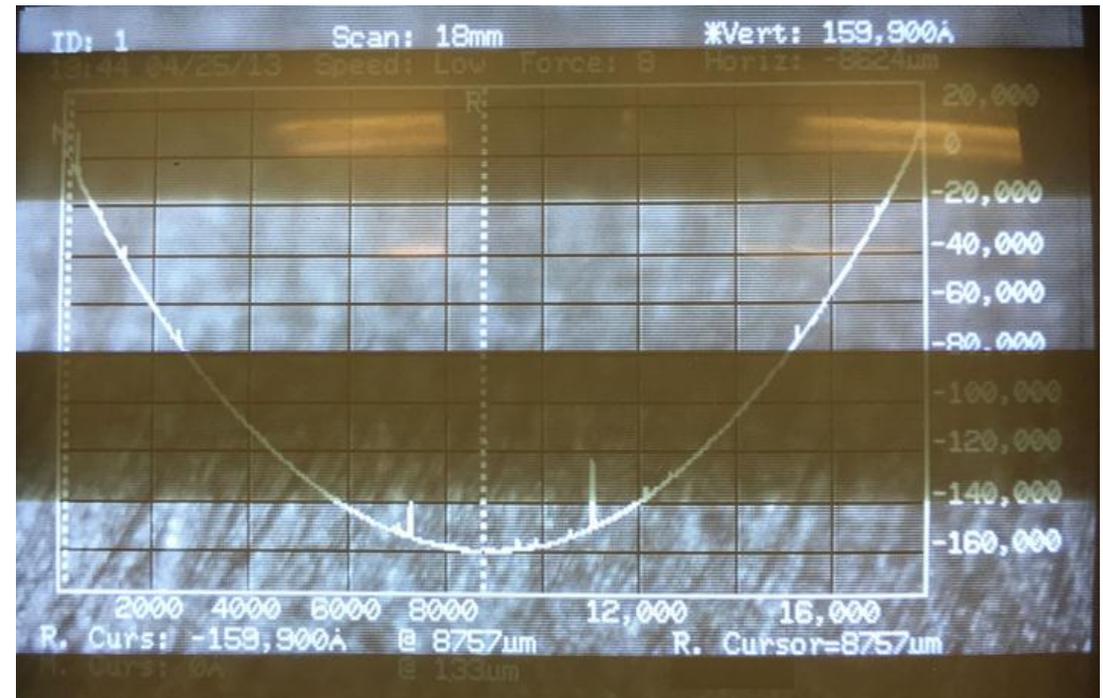


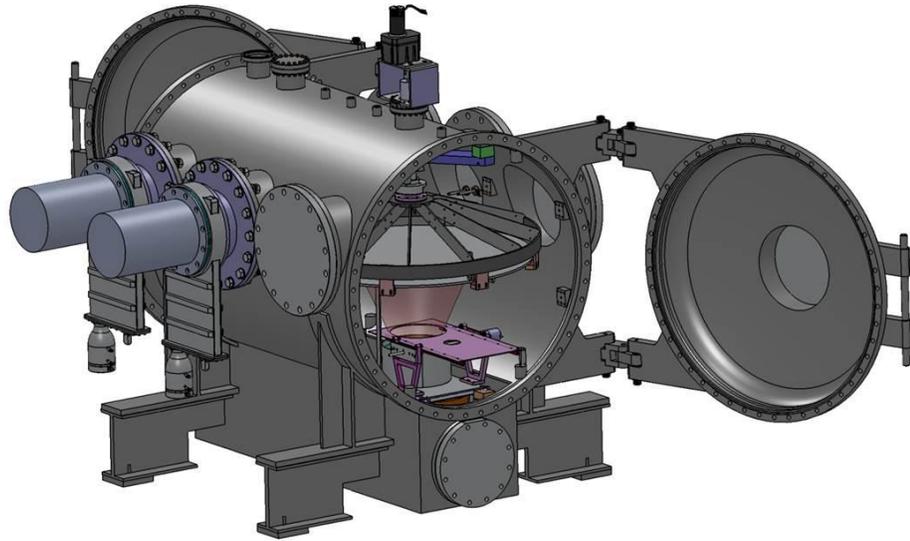
Calculating Stress (goal is less than 85 MPa)

Profilometry measurement shows ~11 microns of Si



1 inch diameter, 20-mil fused silica disc bent 16-microns = ~60 MPa (tensile)

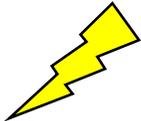




ZeCoat's 1.2-m vacuum coating chamber was completed in March, 2013 and utilizes an ion-assisted e-beam evaporation system

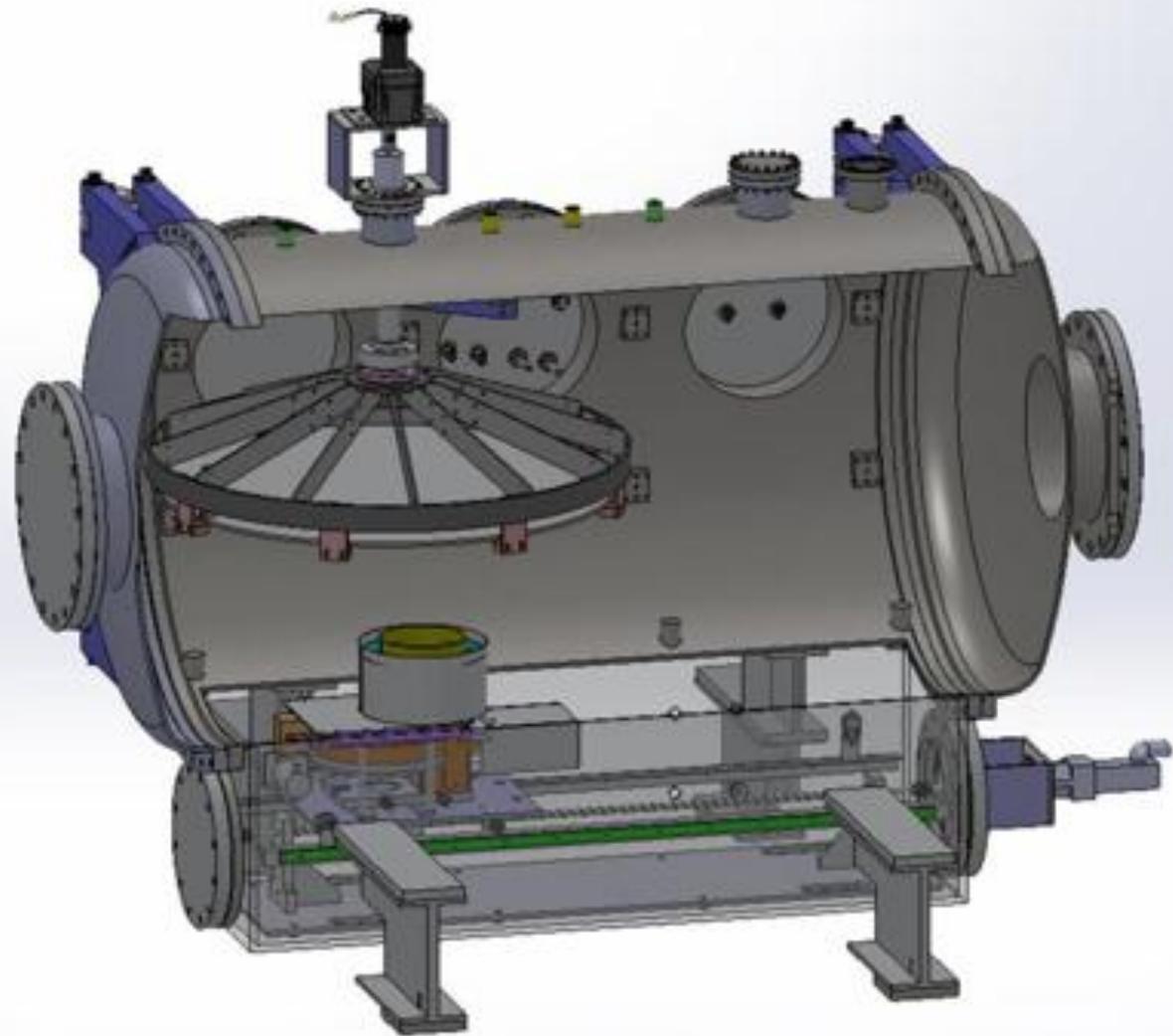


Phase I & II Challenges

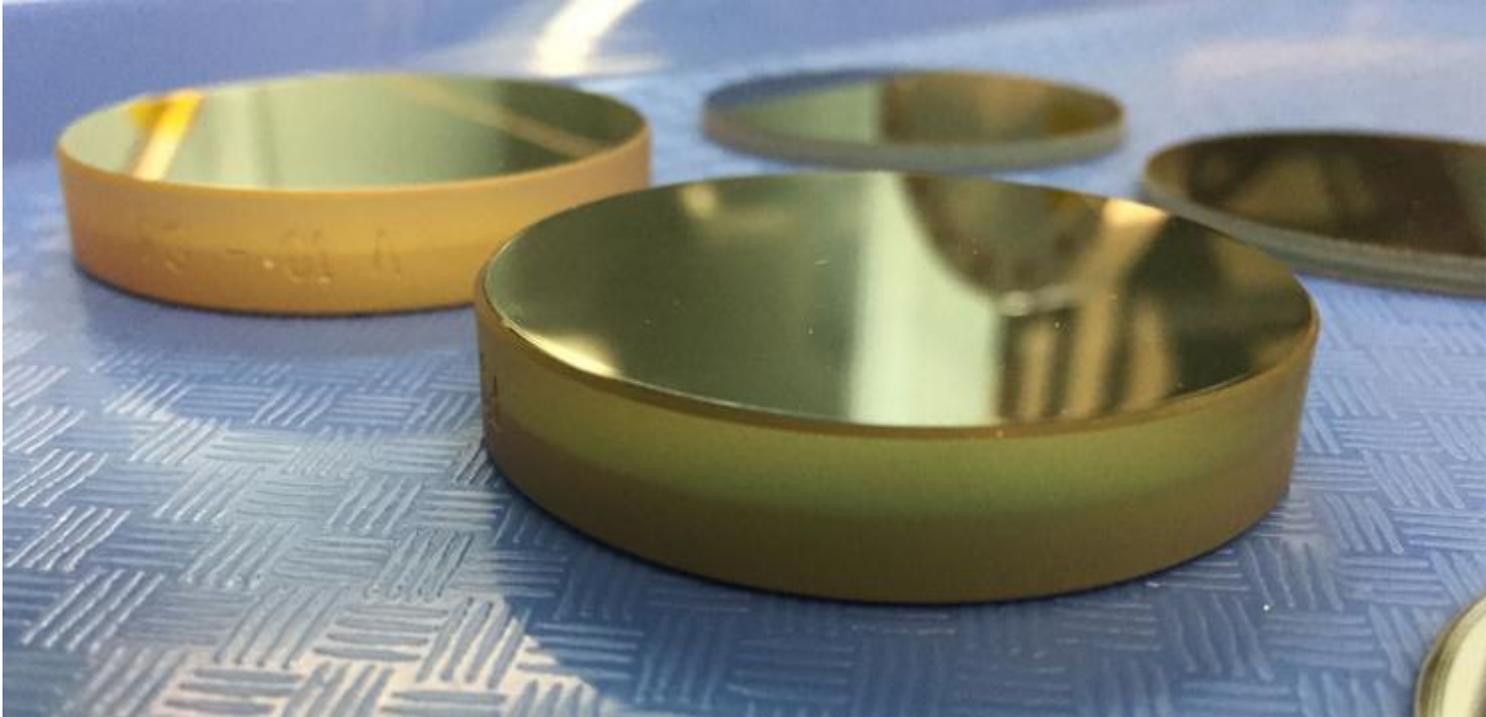
- Surface defects
 - A spitting event is when molten silicon explodes from the evaporation crucible potentially damaging the silicon clad surface.
 - Pre-conditioning
 - Excessive evaporation rates, e-beam “digging”
 - Dust; opening and closing the chamber many times during the process to replenish materials, etc.
- Arcing 
 - Arcs associated with ebeam evaporation (high voltage discharges within the chamber) cause many problems

Overcoming Arcing Problems

- Designed and installed new shielding over the electron emitter assembly
- New shielding over ceramic insulators
- Ground wires far from high-voltage lines
- Installed relays between the computer system and process sensors within the chamber, to isolate the computer from arcing interference
- Wrote new motion control software to detect false signals due to arcing and reset the computer system seamlessly



Silicon Polishing Tests



Polishing Results Phase I and Phase 2 (1st Q)

Scan length 1024 microns						
						goal < 5
Project	ID	Substrate	Evap. Rate	Si Thickness (μ)	PTV (A)	RMS (A)
Phase I	1a	SiC (rough)	3x	20	16	2.8
Phase I	1b	SiC (rough)	3x	20	236	21.5
Phase I	1c	SiC (rough)	3x	20	460	36.7
Phase I	2a	SiC (rough)	3x	20	137	21.4
Phase I	2b	SiC (rough)	3x	20	84.2	10.8
Phase I	2c	SiC (rough)	3x	20	314.1	24.4
Phase II	SN1	Fused Silica (polished)	1x	4	9.2	1.4
Phase II	SN3	Fused Silica (polished)	1x	11	23.3	3.2

Surface Roughness Profile

Silicon Coated Sic Sub #1 B

Processed

RMS 21.53 angstroms

P-V 236.78 angstroms

Points 1024 microns

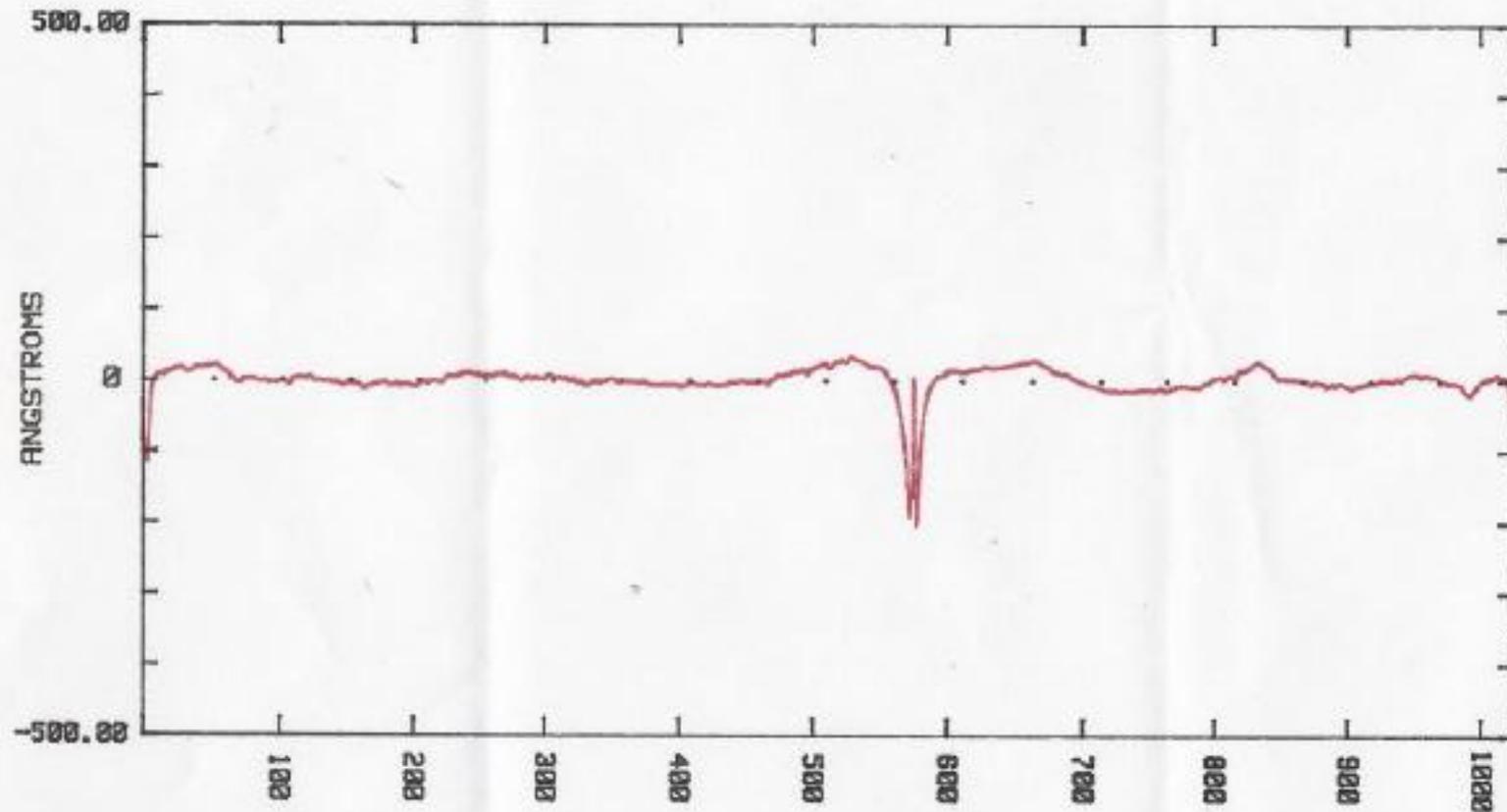
Coastline Optics, LLC

906 Via Alondra

Camarillo, CA 93012

(805) 384-8609

28 Oct 2013 14:17:34



Surface Roughness Profile

Silicon Coated Sic Sub #1 C

Processed

RMS 36.65 angstroms

P-V 459.52 angstroms

Points 1024 microns

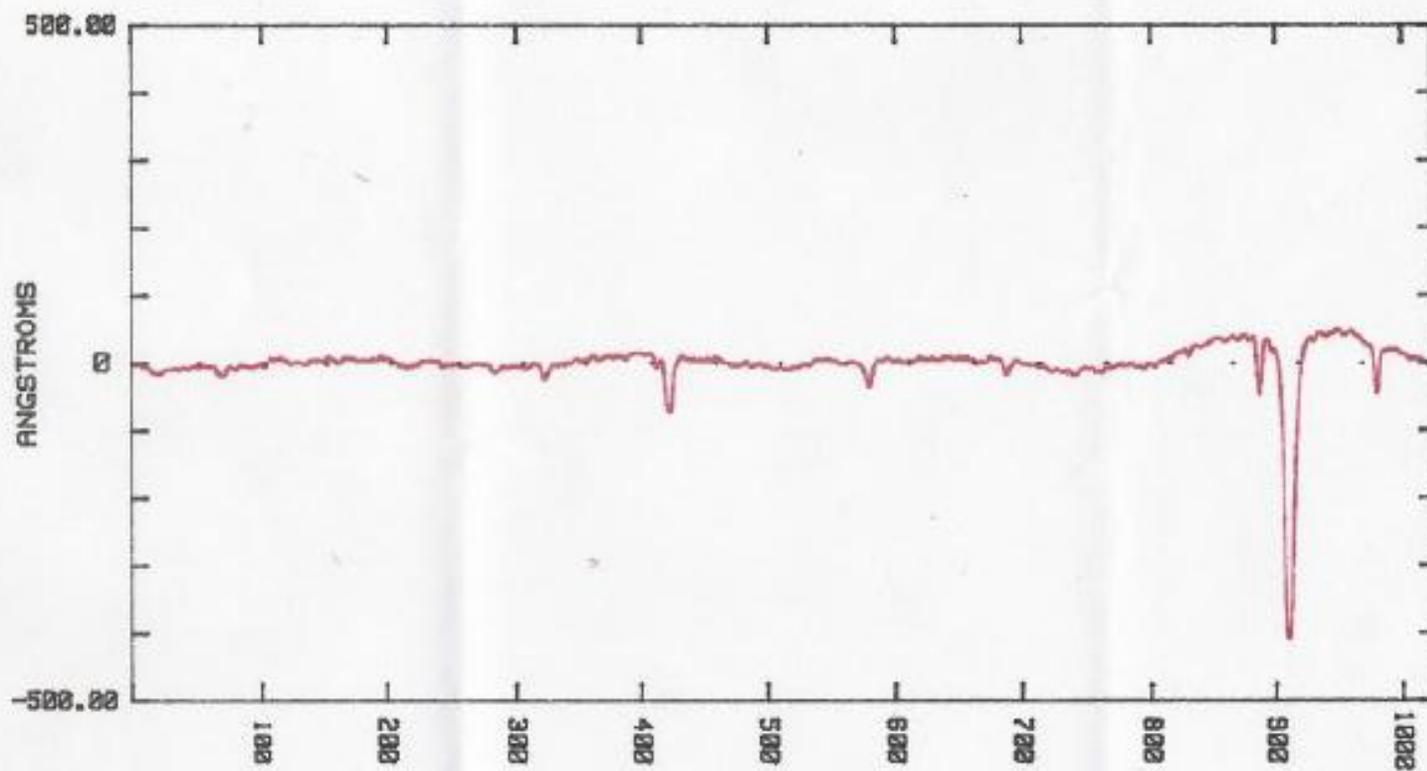
Coastline Optics, LLC

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Surface Roughness Profile

FS-03

Processed

RMS 3.24 angstroms

P-V 23.32 angstroms

Points 1024 microns

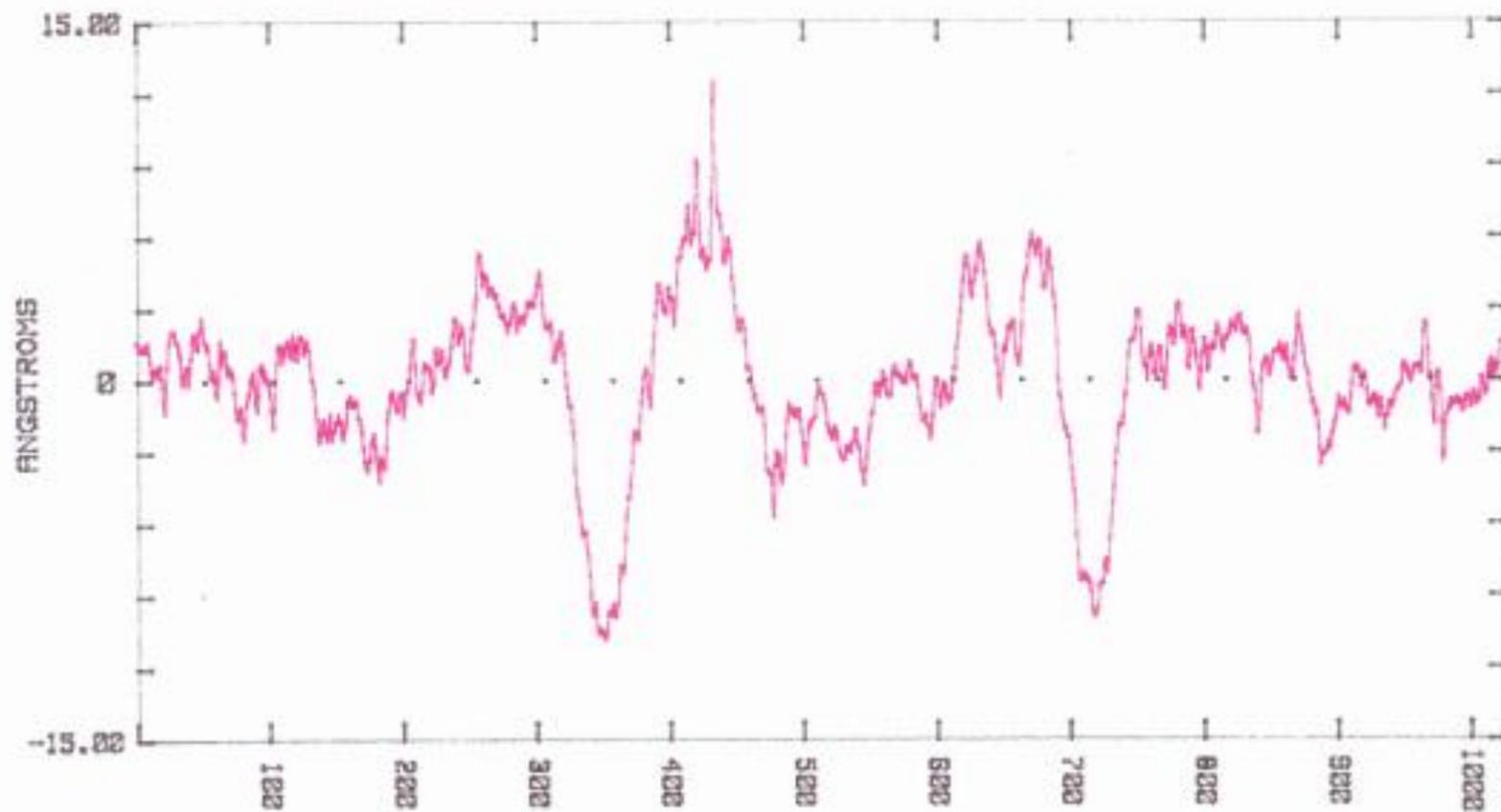
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Surface Roughness Profile

FS-01

Processed

RMS 1.36 angstroms

P-V 9.19 angstroms

Points 1024 microns

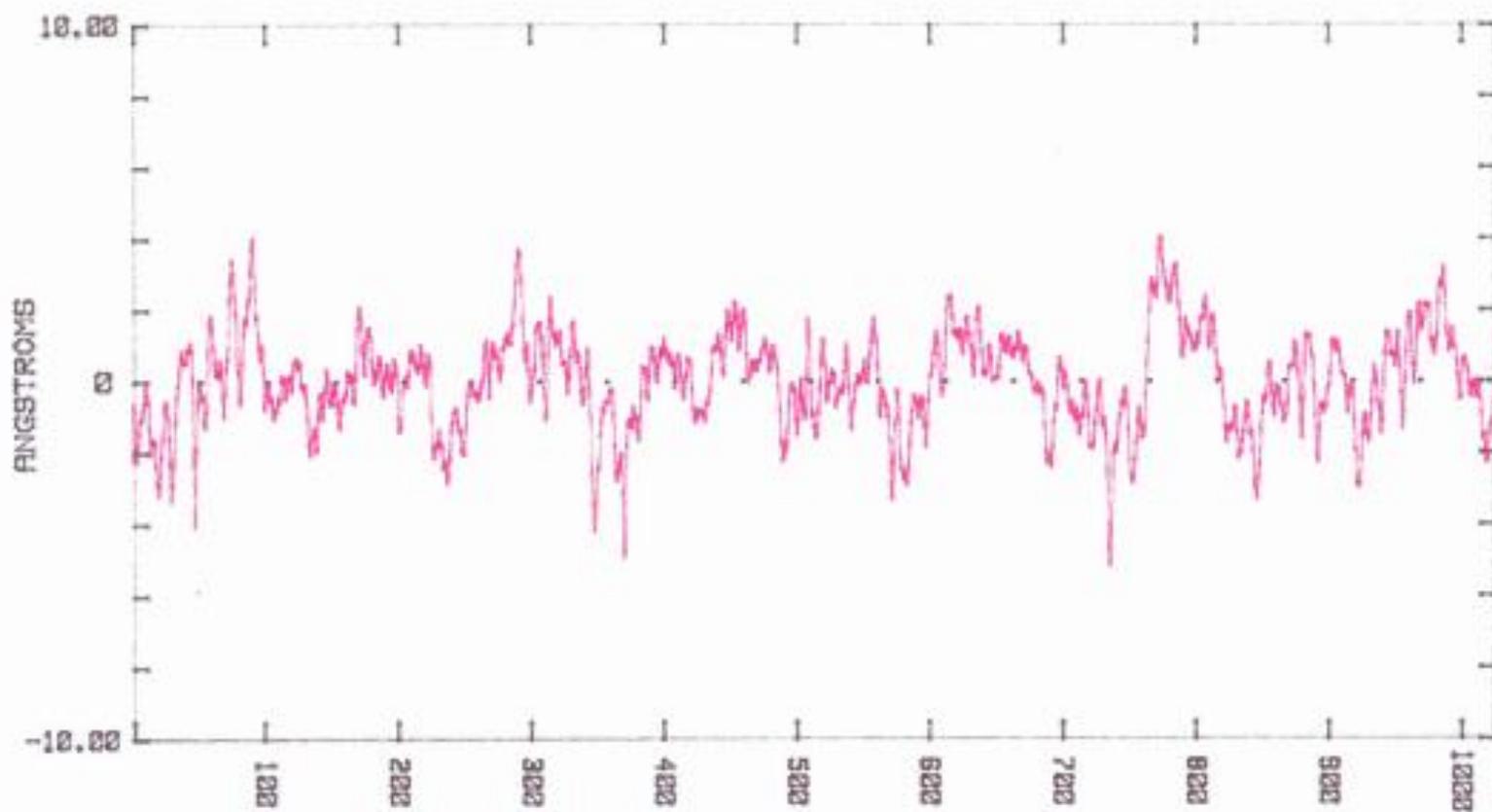
Coastline Optics, LLC

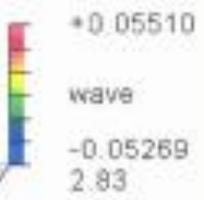
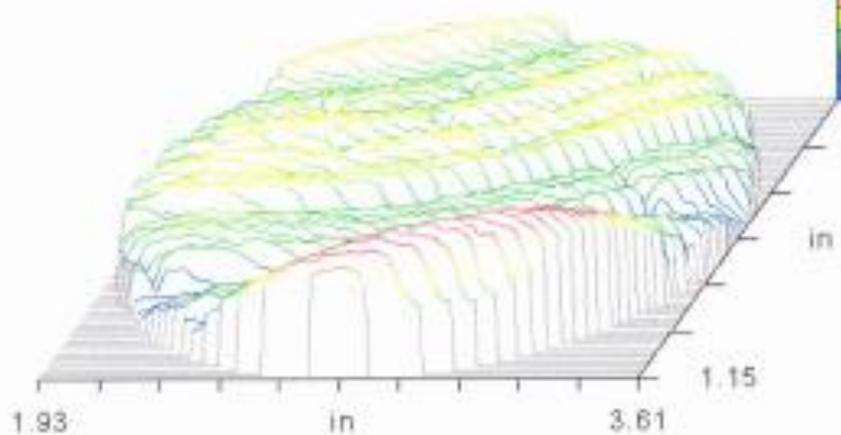
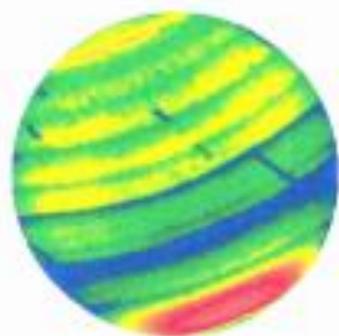
986 Via Alondra

Camarillo, CA 93012

(805) 384-2689

11 Nov 2014 14:43:41





PV	0.1078	wave
rms	0.0160	wave
Power	0.0083	wave
Removed: PST TLT		

Data Points	31177
Rad	-43535.7
	μ

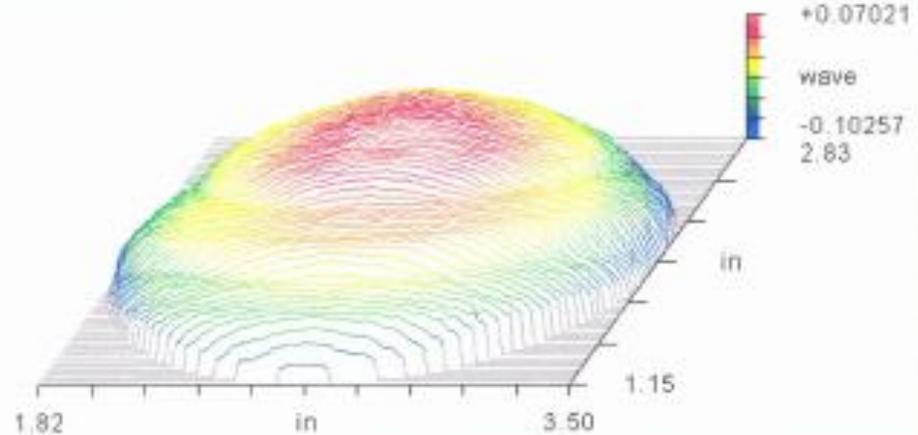
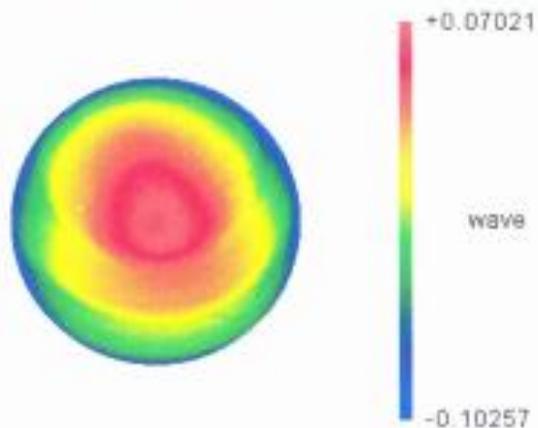
Auto Aperture:	Off
Aperture OD (%)	90

Trim Filter:	Off
Trim Mode:	Outside
Trim Quantity:	0

Filter:	Off	Filter Window Size:	3
Filter Type:	Average		



Desc:	2.0 Si Coated FS Sub	AGC:	On	Light Level:	185
S/N:	FS-03	AGC Mode:	Normal Reflectivity		
Inspector:	K. Chavez	Acquisition Mode:	Phase		
Wavelength-In:	632.8 nm	Phase Resolution:	High		
Wavelength-Out:	632.8 nm	Phase Avg:	4	Intens. Avg:	1
Refractive Index of Material:	1.500	Camera Res:	640x480 25 Hz		



PV 0.1728 wave

rms 0.0383 wave

Power -0.1290 wave

Removed:
P81 TLT

Data Points 31177

Rad 2807.4 m

Auto Aperture: Off

Aperture OD (%): 90

Trim Filter: Off

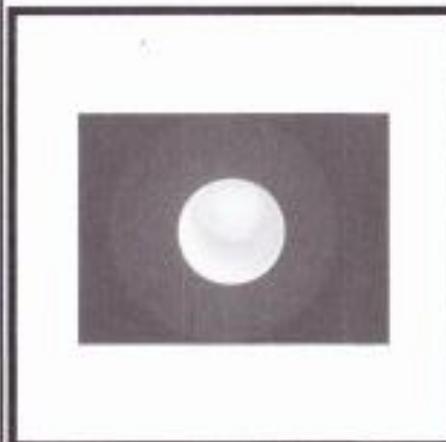
Trim Mode: Outside

Trim Quantity: 0

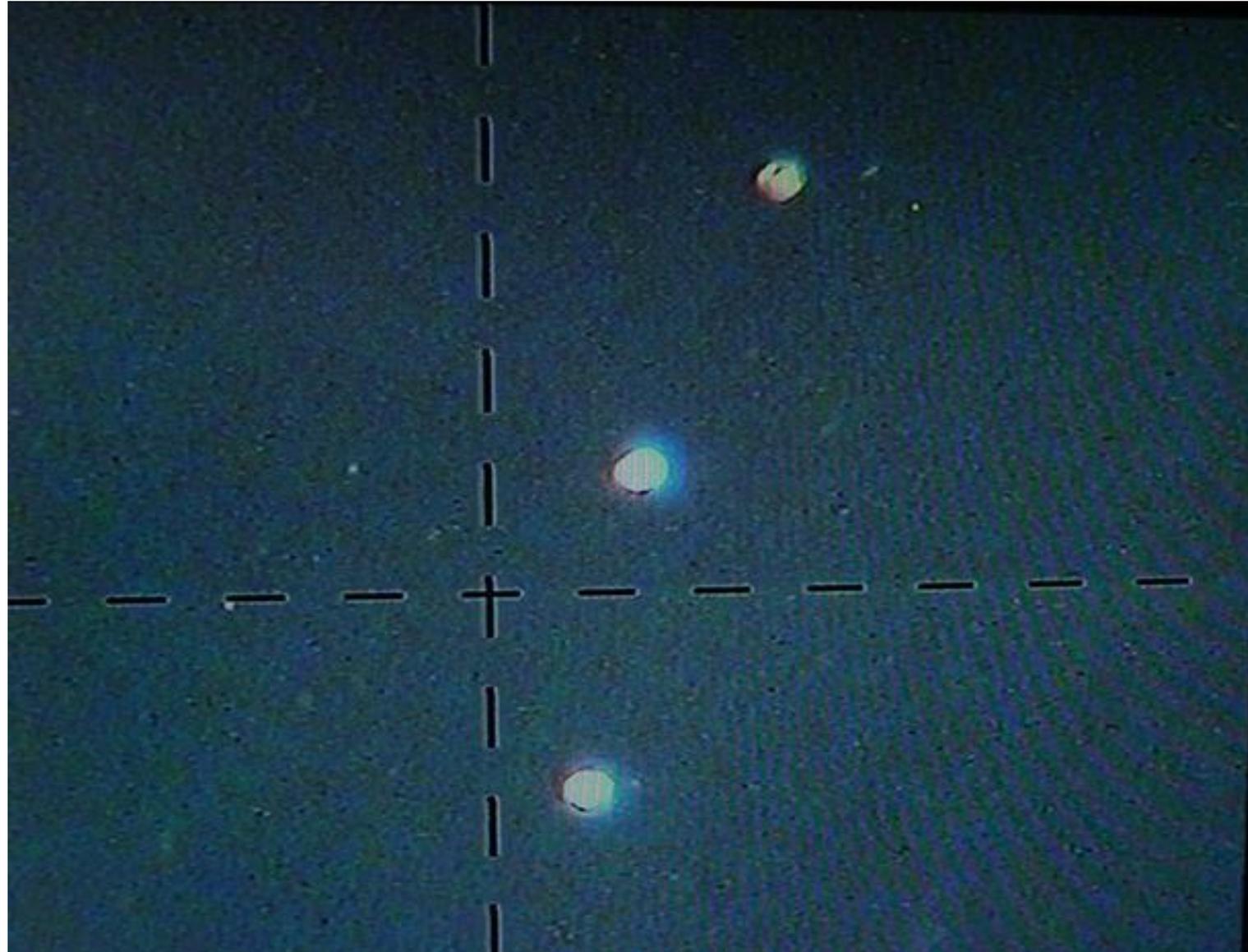
Filter: Off

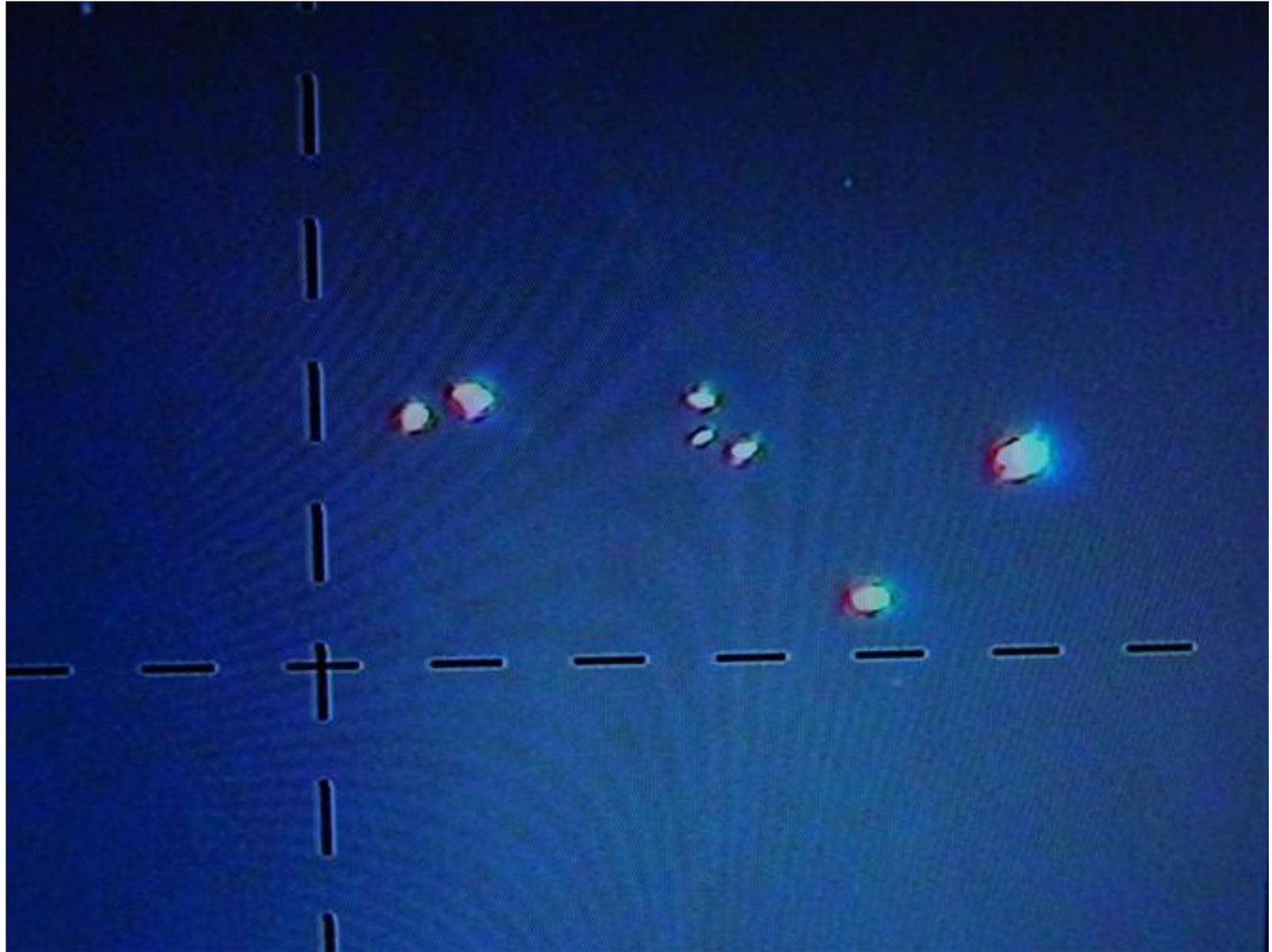
Filter Window Size: 3

Filter Type: Average

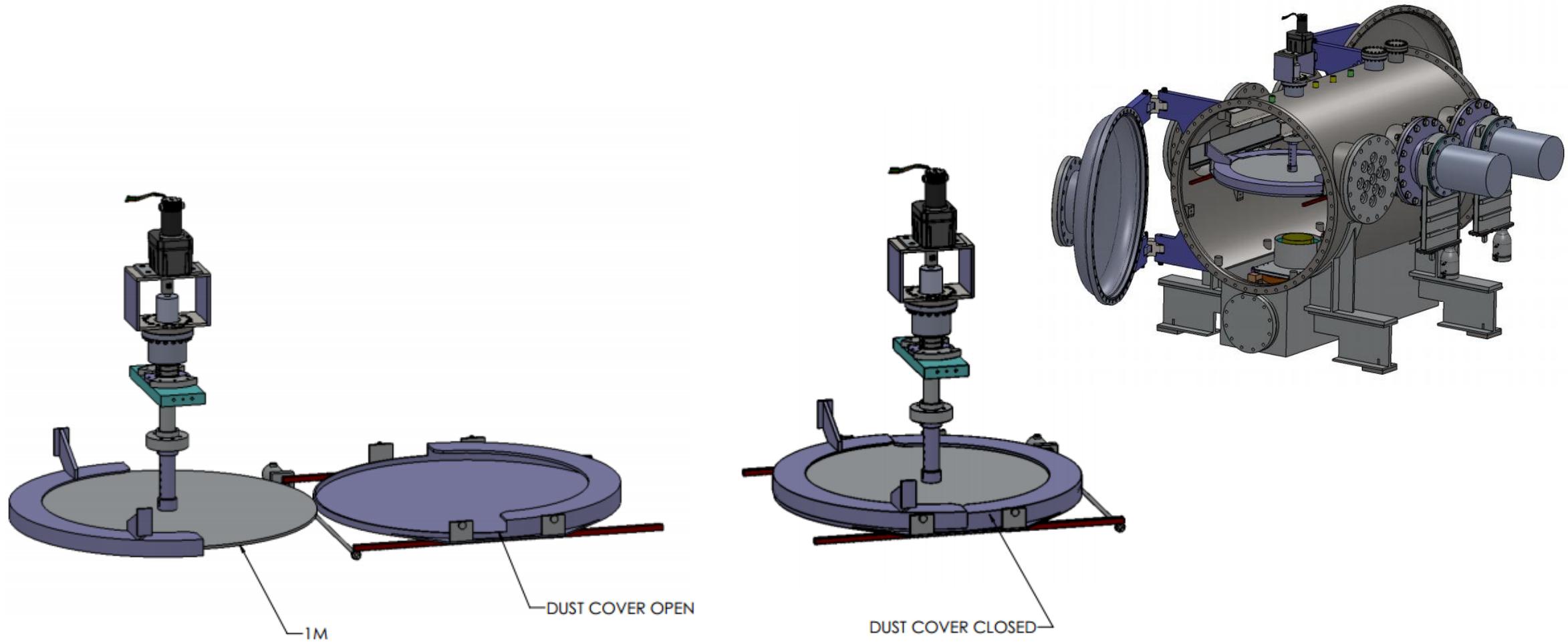


Desc: 2.0 Si Coated P8 Sub	AGC: On	Light Level: 185
S/N: P8-D1	AGC Mode: Normal Reflectivity	
Inspector: K. Chavez	Acquisition Mode: Phase	
Wavelength-In: 632.8 nm	Phase Resolution: High	
Wavelength-Out: 632.8 nm	Phase Avg: 4	Intens Avg: 4
Refractive Index of Material: 1.500	Camera Res: 640x480 25 Hz	
Substrate System Error: Off	Discon Action: Filter	
System Error File: 12IntFlat.dat	Discon Filter: 0	
	Interferometer Scale Factor: 0.500	
Inst: Mark GPI Id 0 SN 004157	Date: Tue Nov 11 14:38:44 2014	





Motorized Dust Cover Inside Vacuum Chamber



Alternatives to heating with an electron beam? Possible advantages (higher rates?, reduced surface defects?)

Thermal resistive Ta source (1800 C)



Inductive heating



Resistive graphite heating
(3000 C)



Other things to investigate?

- Cold-cathode neutralization of the ion gun?
 - Process duration is currently limited because of required ion gun maintenance (neutralization filament replacement)
- More automation
 - Rate control
 - Automate ion gun turning on off
 - Crucible changes (heat up and cool down)
- How to remove the silicon for re-work?
 - Chemical removal
 - Micro-gritblasting

Questions?